Scaling Trends for Dual-Rail Logic Styles against Side-Channel Attacks: a Case-Study



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Outline

- Motivation
- Shrink but Think...
- Countermeasures against SCA
- Contributions
- Performance evaluation methodology
- Security evaluation methodology
- Simulation Parameters
- Security analysis
- Conclusion

Internet of things



Courtesy: i-scoop.com

Side-Channel Attacks



Courtesy: venturebeat.com

To Moore' and Beyond...



Scaling – but Thinking security





















Thanks to dual-rail logic, we deal with signal reduction and achieve lower signals compared to CMOS...



CMOS





- Easier to implement
- Lesser area overhead
- Faster design time
- Can be implemented using standard cell libraries

Vulnerable to side-channel attack as power consumption is dependent on manipulated data







DDSLL XOR

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XOR CMOS

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 Ideally equalized power consumption irrespective of manipulated data

CMOS vs Dual-rail logic Operation



I_{DD} in CMOS

CMOS vs Dual-rail logic Operation



 I_{DD} in CMOS



Phase	Clk	Inputs	Outputs
Precharge	Low	Don't care	High
Evaluation	High	Valid	Valid













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Imbalances in capacitances (dual-rail logics) lead to data dependencies which become exploitable [34,19,26,29,16] Does it get **worse** *with scaling?*



Implementation







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AES 8-bit S-box

- CMOS styles implemented in 65nm and 28nm
- DDSLL styled using BDD implemented in 65nm and 28nm



Evaluation

Low power operation

 All S-boxes operated from nominal voltage of technology to (nominal voltage – 500 mV)



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Evaluation

Performance Metric

- Energy-per-operation
- SNR

Distinguisher

- Points-of-Interest
- (PCA and Maximum signal)
 Noise level
- Noiseless

 Cautionary note: no routing parasitics or PVT variations are considered, so this is the ideal case; when included it should only add to the performance degradation in dual rail circuits.

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 - Voltages are also scaled from nominal to nominal-0.5V
 - Energy per operation, a relatively discriminant metric, is used for performance comparison since it integrates the total power over the time.

$$E_{op} = \int_{t} (P_{dyn} + P_{stat}) dt,$$

= $\underbrace{\frac{1}{2} N_{sw} C_L V_{DD} V_{swing}}_{\text{Dynamic}} + \underbrace{V_{DD} I_{leak} T_{del}}_{\text{static}},$

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Since we have *noise-free* traces, we compute only the numerator corresponding to *maximizing* the signal,

$$\hat{\mathsf{var}}_x(\hat{\mathsf{E}}_i(L^i_x))$$

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 - > Random 1000-bit input signal for E_{op} calculation
 - > signal, S_{PCA} and energy per operation, E_{op} w.r.t V_{DD} computed

Security analysis

Security vs Performance– PCA applied signal

- The x-axes represents the Energy per operation <u>ratio</u> between CMOS & DDSLL, i.e $\frac{E_{op}^{CMOS}}{E_{op}^{DDSLL}}$
- The y-axes represent the <u>ratio</u> of the PCAapplied Signal between CMOS & DDSLL, i.e $\frac{S^{PCA}_{CMOS}}{S^{PCA}_{DDSLL}}$

Scaling Trends-CMOS/DDSLL- 65nm/28nm

Security vs Performance-PCA applied signal



- Nominal voltage for 65nm technology is 1.2V (1.2-0.7V)
- Nominal voltage for 28nm technology is 1V (1 0.5V)

Scaling trends for CMOS - Performance

Scaling trends for CMOS E_{op}



Scaling trends for CMOS - Security

Scaling trends for CMOS signal



Conclusion

- Interest in DDSLL over CMOS vanishes as circuit sizes shrink.
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- SNR reduction via signal reduction is likely to become increasingly challenging.
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- SNR reduction via signal reduction is likely to become increasingly challenging.
 - By contrast, scaling trends are positive for CMOS because of increase in (intrinsic) noise.
- Designing efficient and noisy CMOS implementations is an interesting research challenge
 - Dual-rail logics may still be useful for other purposes such as ensuring independence for masking

Thank you